Features

- Trench Power LV MOSFET Technology
- High Density Cell Design for Low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

Dual N&P-Channel MOSFET

Maximum Ratings

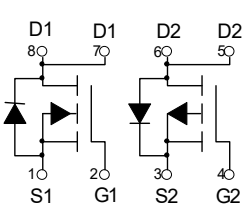
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 78°C/W Junction to Ambient(Note2)

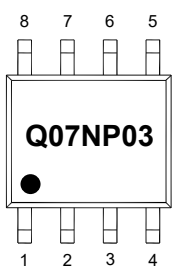
Parameter		Symbol	Rating	Unit
Total Power Dissipation(Note3)		P_D	1.6	W
N-Channel				
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	7	A
	T_A=70°C		5.6	
Pulsed Drain Current (Note4)		I_{DM}	28	A
P-Channel				
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	-7	A
	T_A=70°C		-5.6	
Pulsed Drain Current (Note4)		I_{DM}	-28	A

Note:

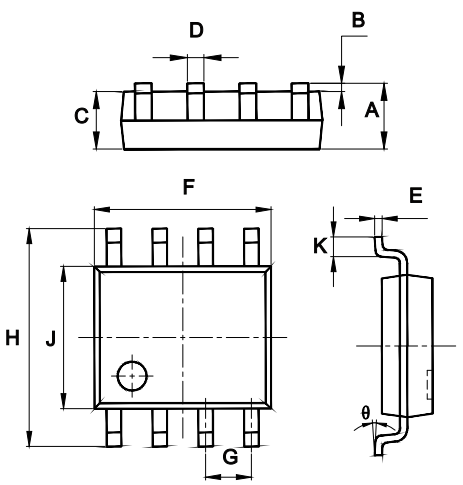
1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R_{thJA} is measured with the device mounted on 1 in2 FR-4 board with 2oz. copper, in a still air environment with T_A=25°C
3. P_D is based on max. junction temperature, using junction-ambient thermal resistance.
4. Repetitive rating; pulse width limited by max. junction temperature.

Internal Structure and Marking Code



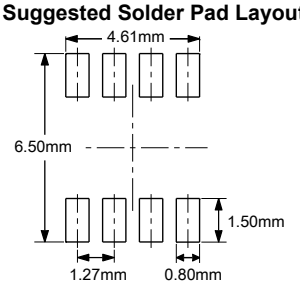


SOP-8



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.053	0.069	1.35	1.75	
B	0.004	0.010	0.10	0.25	
C	0.053	0.061	1.35	1.55	
D	0.013	0.020	0.33	0.51	
E	0.007	0.010	0.17	0.25	
F	0.185	0.200	4.70	5.10	
G	0.050		1.270		TYP.
H	0.228	0.244	5.80	6.20	
J	0.150	0.157	3.80	4.00	
K	0.016	0.050	0.40	1.27	
θ	0°	8°	0°	8°	

Suggested Solder Pad Layout



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N-Channel MOSFET Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1	1.5	2.2	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=6A		15	18	mΩ
		V_{GS}=4.5V, I_D=5A		23	30	
Gate Resistance	R_G	f=1MHz, Open drain		1.7		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				7	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=6A			1.2	V
Reverse Recovery Time	t_{rr}	I_F=5.6A, dI_F/dt=100A/μs		11		ns
Reverse Recovery Charge	Q_{rr}			3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHz		357		pF
Output Capacitance	C_{oss}			70		
Reverse Transfer Capacitance	C_{rss}			60		
Total Gate Charge	Q_g	V_{DS}=15V,V_{GS}=10V,I_D=5.6A		8.5		nC
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}			2		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=15V, V_{GS}=10V, R_G=3Ω, I_D=5.6A		5		ns
Turn-On Rise Time	t_r			4		
Turn-Off Delay Time	$t_{d(off)}$			12		
Turn-Off Fall Time	t_f			3		

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P-Channel Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=-250μA	-30			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V, V_{GS}=0V			-1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V, I_D=-6A		17	23	mΩ
		V_{GS}=-4.5V, I_D=-5A		22	34	
Gate Resistance	R_G	f=1MHz, Open drain		10		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				-7	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-6A			-1.2	V
Reverse Recovery Time	t_{rr}	I_F=-7.5A, dI_F/dt=100A/μs		18		ns
Reverse Recovery Charge	Q_{rr}			8		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-15V,V_{GS}=0V,f=1MHz		1623		pF
Output Capacitance	C_{oss}			188		
Reverse Transfer Capacitance	C_{rss}			165		
Total Gate Charge	Q_g	V_{DS}=-15V,V_{GS}=-10V,I_D=-9A		31		nC
Gate-Source Charge	Q_{gs}			4		
Gate-Drain Charge	Q_{gd}			5.5		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=-15V, V_{GS}=-10V, R_G=2.5Ω, I_D=-7.5A		9		ns
Turn-On Rise Time	t_r			13		
Turn-Off Delay Time	$t_{d(off)}$			54		
Turn-Off Fall Time	t_f			25		

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N-Channel MOSFET Curve Characteristics

Fig.1 - Typical Output Characteristics

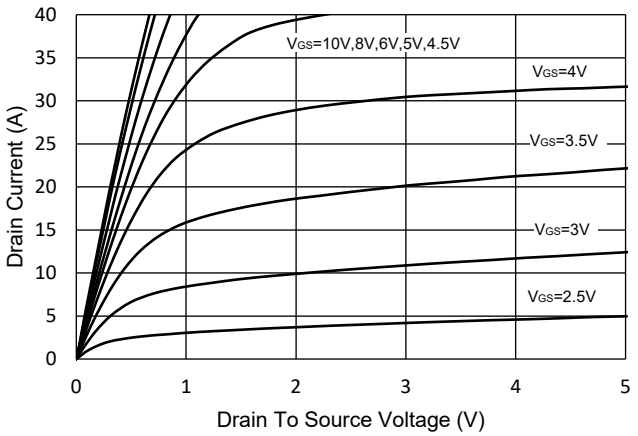


Fig.2 - Transfer Characteristic

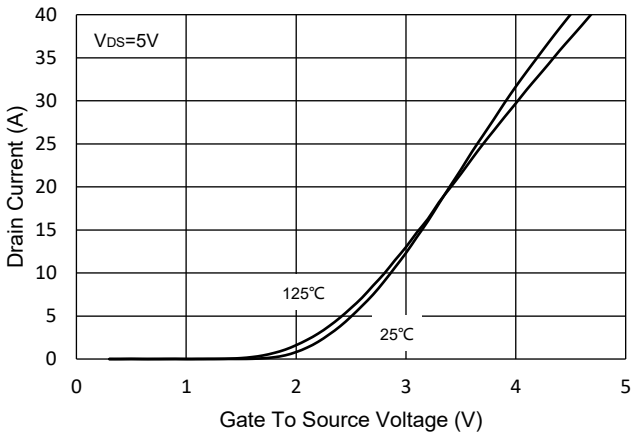


Fig.3 - $R_{DS(ON)}$ - V_{GS}

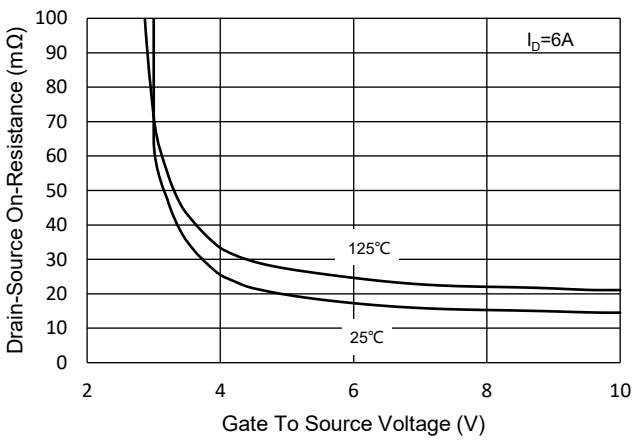


Fig.4 - $R_{DS(ON)}$ - I_D

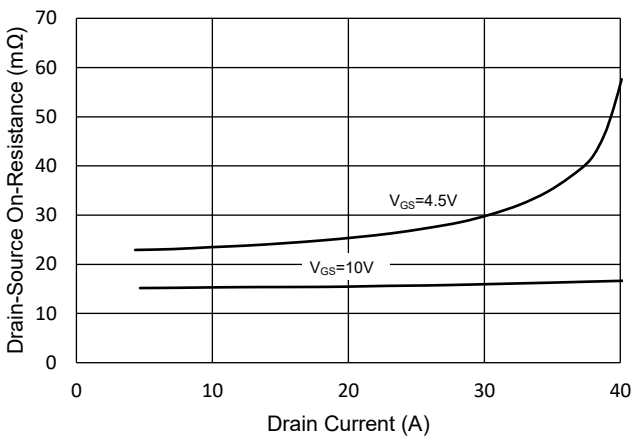


Fig.5 - Capacitance Characteristics

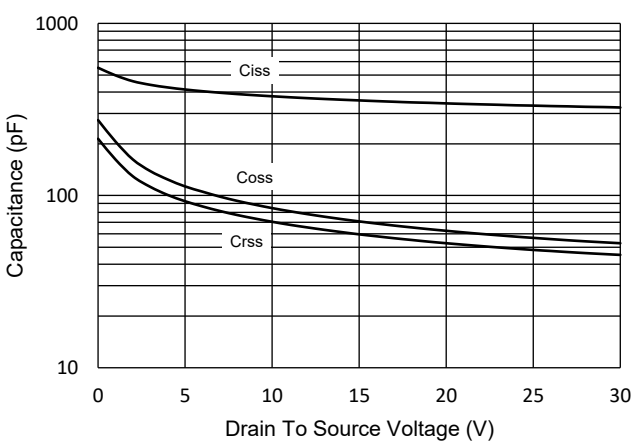
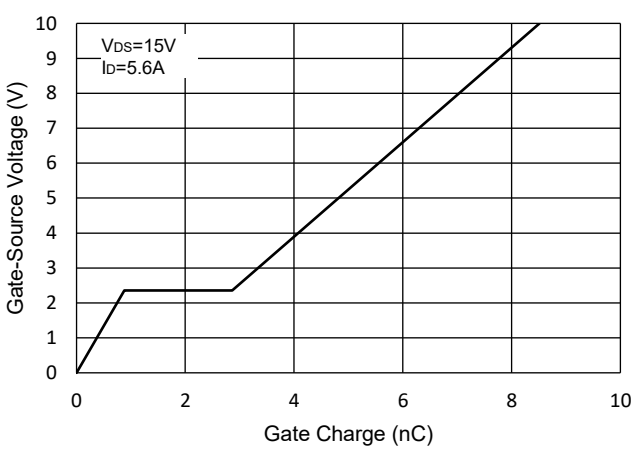


Fig.6 - Gate Charge



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N-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

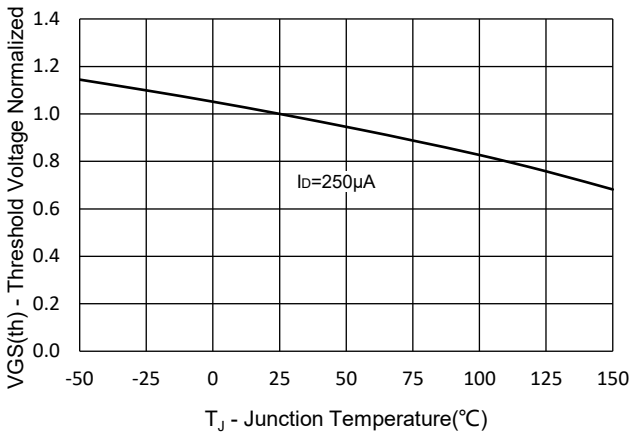


Fig.8 - Normalized On Resistance Characteristics

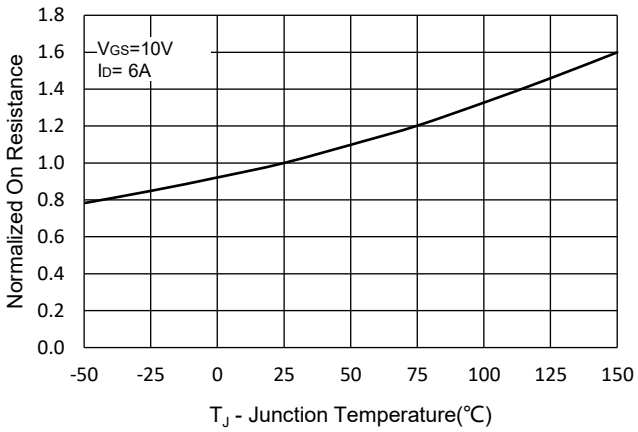


Fig.9 - I_S - V_{SD}

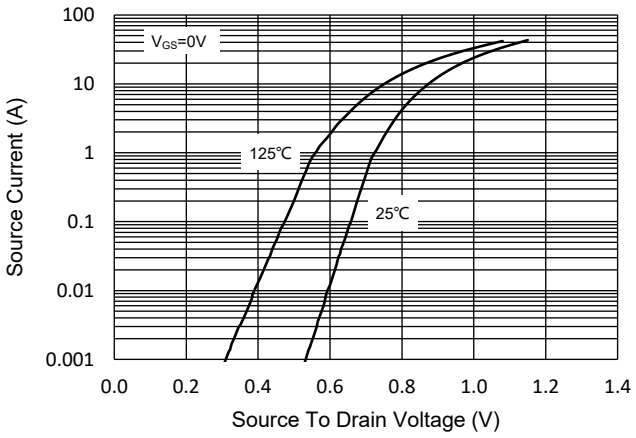


Fig.10 - Drain Current

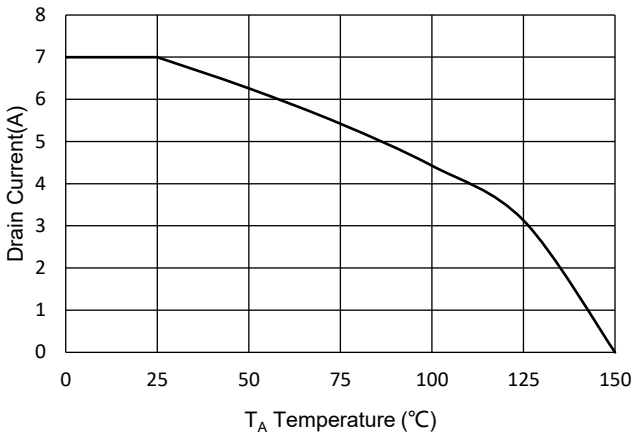
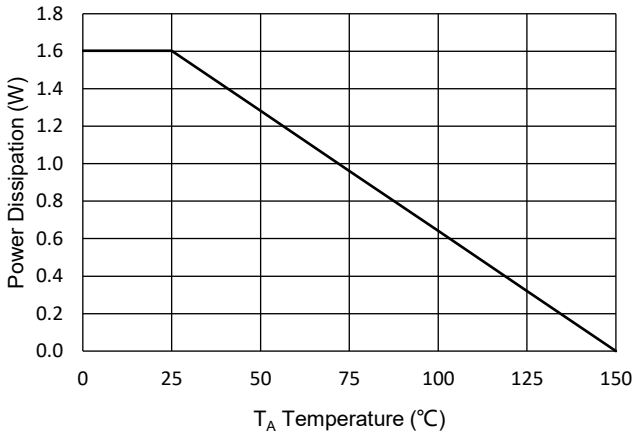


Fig.11 - PD Dissipation



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N-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

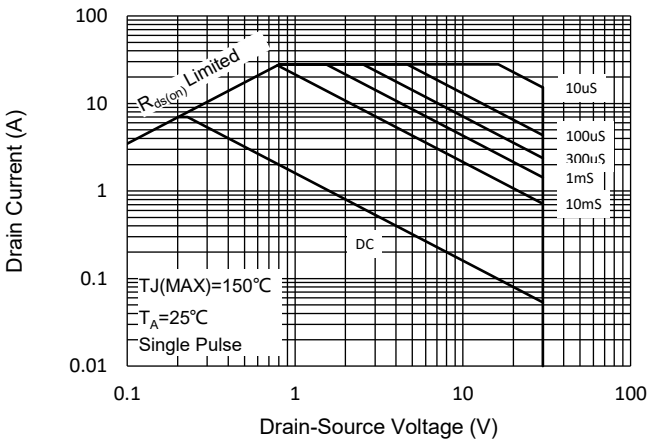
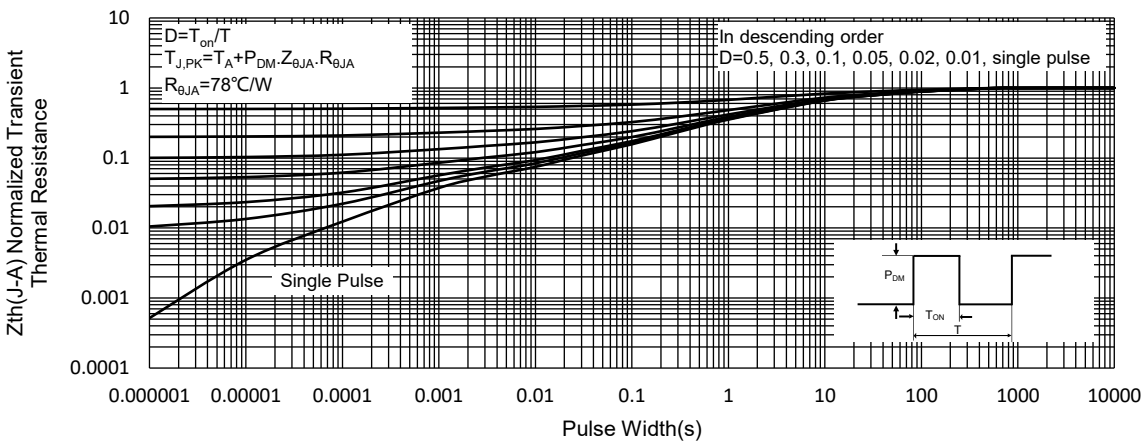


Fig.13 - Normalized Transient Thermal Impedance



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P-Channel MOSFET Curve Characteristics

Fig.1 - Typical Output Characteristics

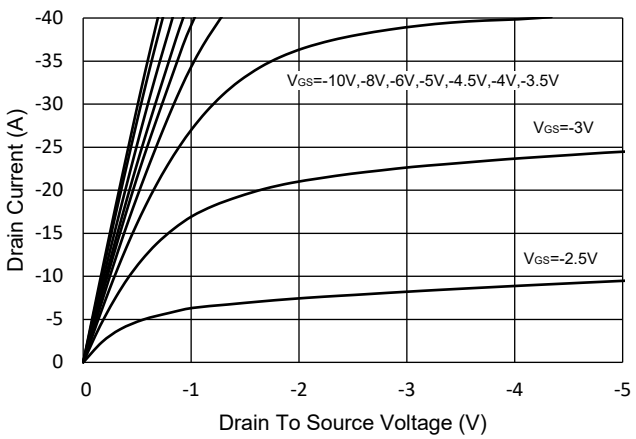


Fig.2 - Transfer Characteristic

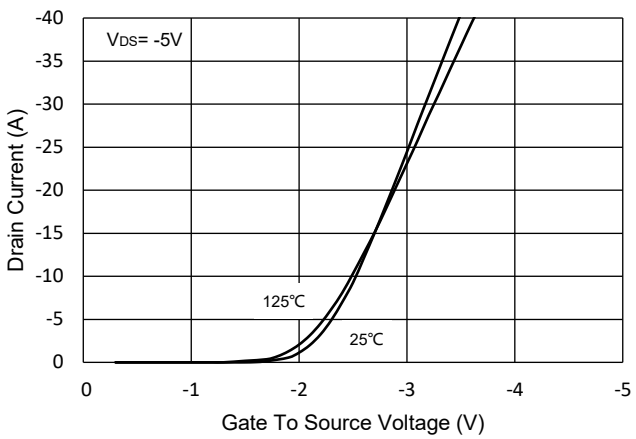


Fig.3 - $R_{DS(ON)}$ - V_{GS}

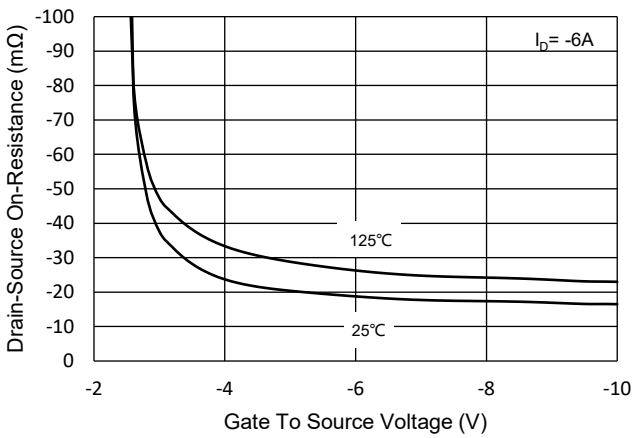


Fig.4 - $R_{DS(ON)}$ - I_D

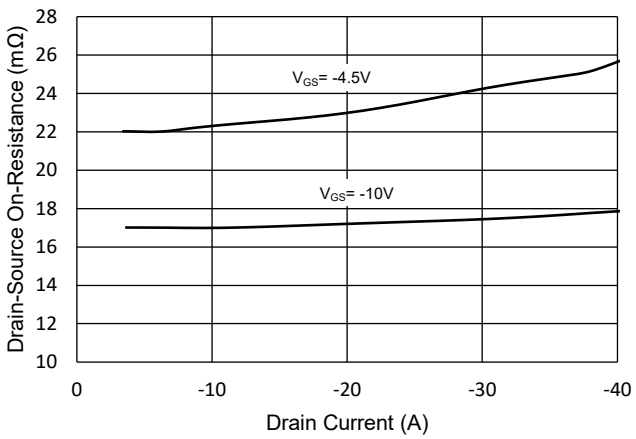


Fig.5 - Capacitance Characteristics

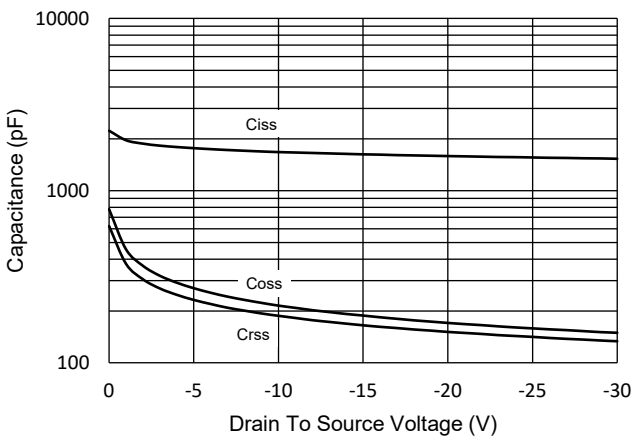
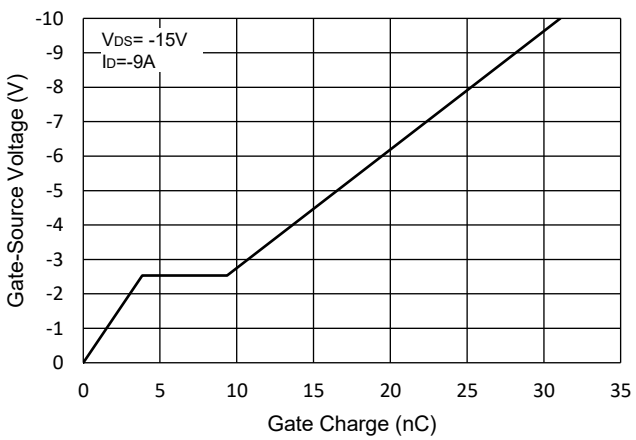


Fig.6 - Gate Charge



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P-Channel MOSFET Curve Characteristics

Fig.7 - Normalized Threshold Voltage

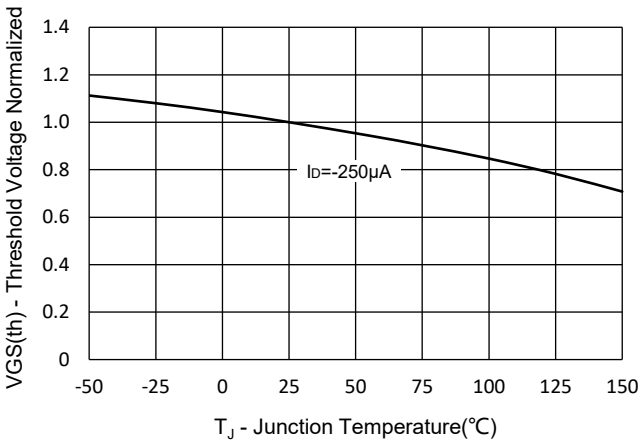


Fig.8 - Normalized On Resistance Characteristics

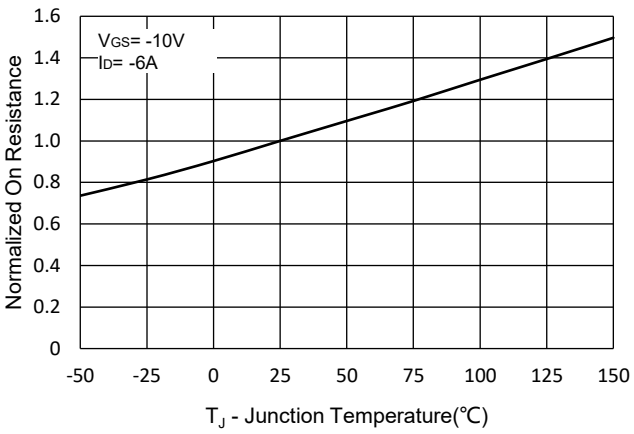


Fig.9 - I_S - V_{SD}

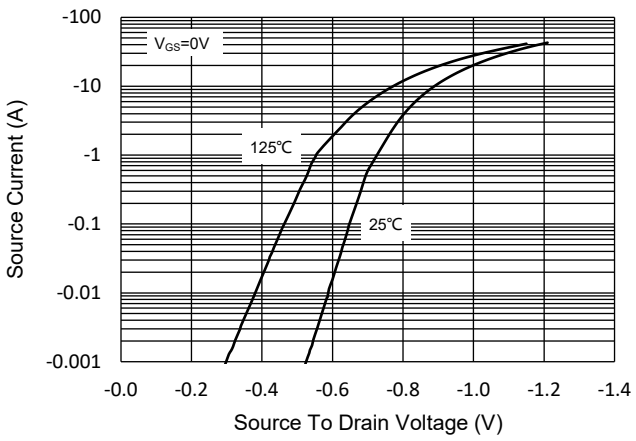


Fig.10 - Drain Current

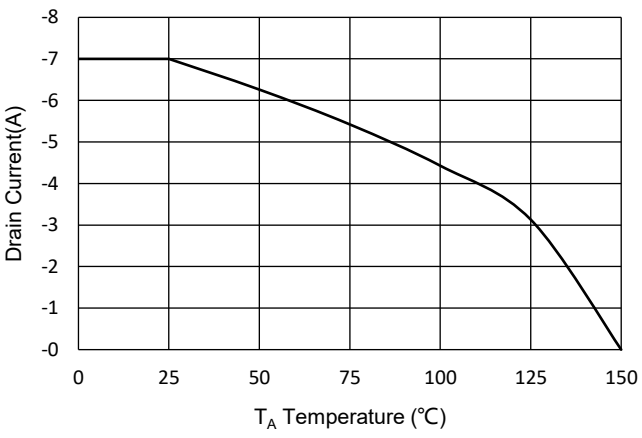
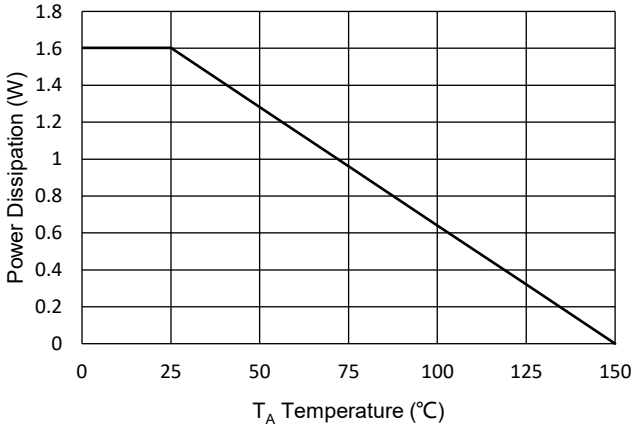


Fig.11 - PD Dissipation



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P-Channel MOSFET Curve Characteristics

Fig.12 - Safe Operation Area

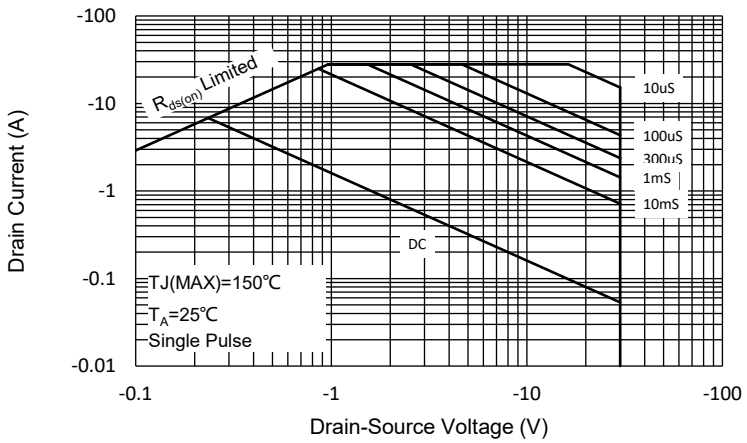
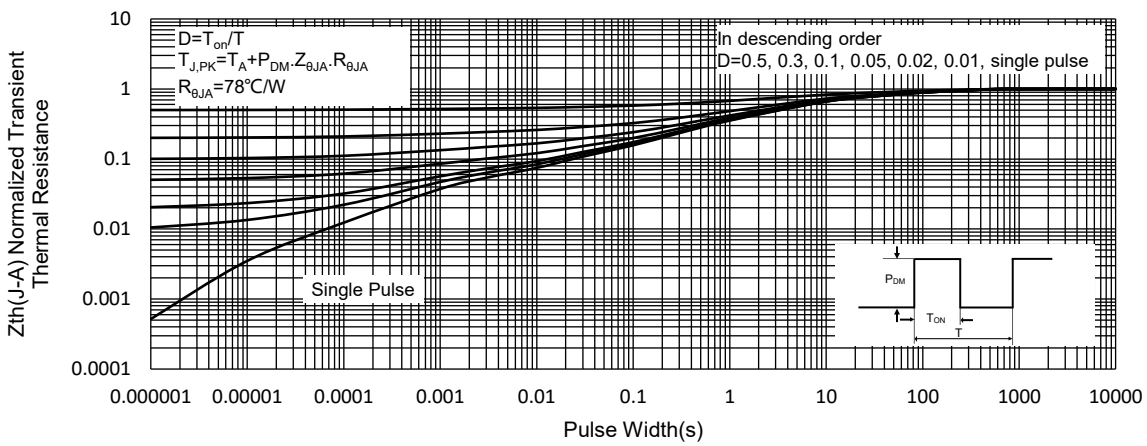


Fig.13 - Normalized Transient Thermal Impedance



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Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 4Kpcs/Reel

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